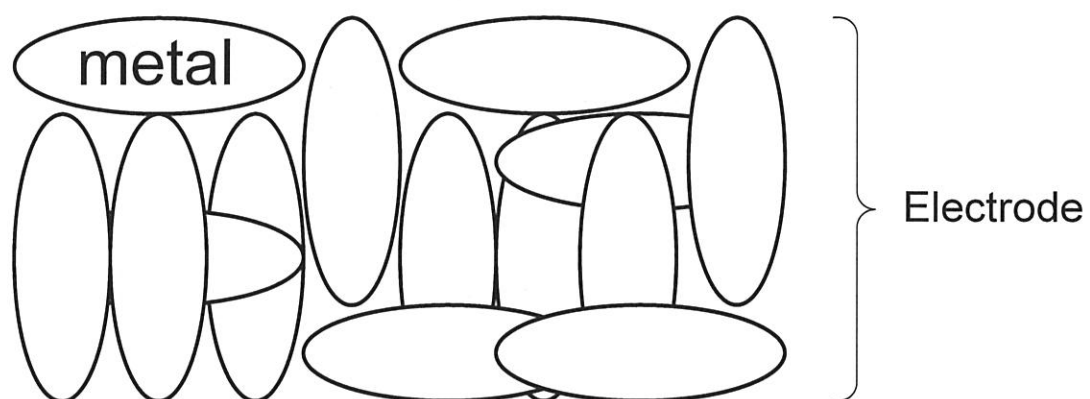
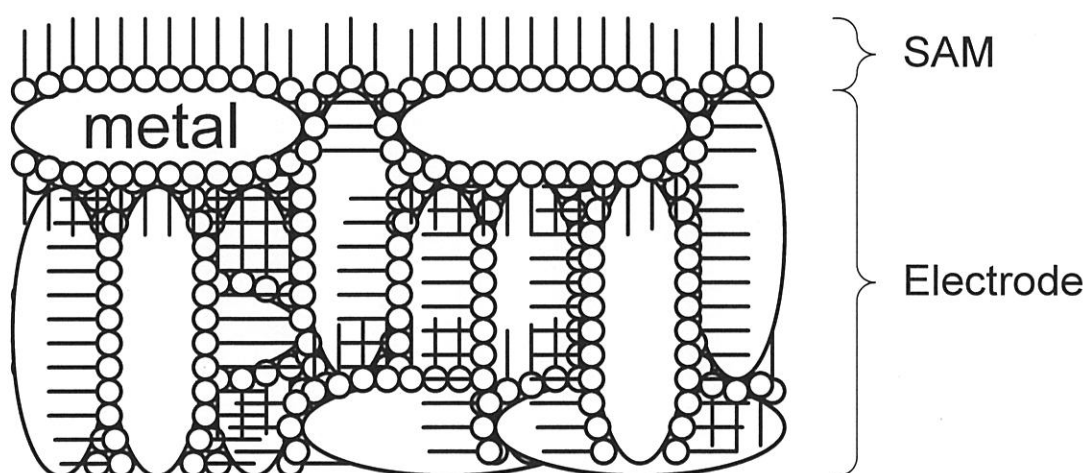


FIG. 1

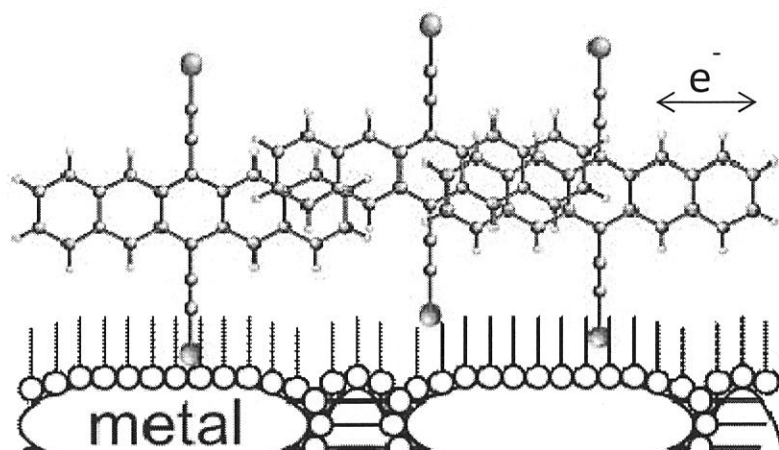
(A)



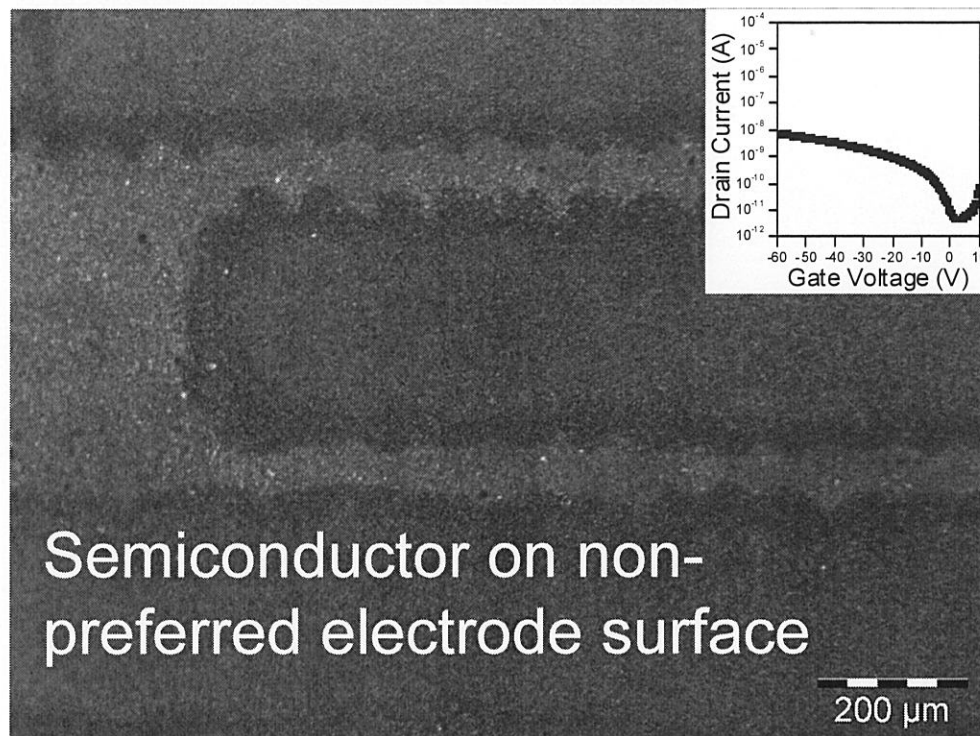
(B)



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FIG. 2



(A)



(B)

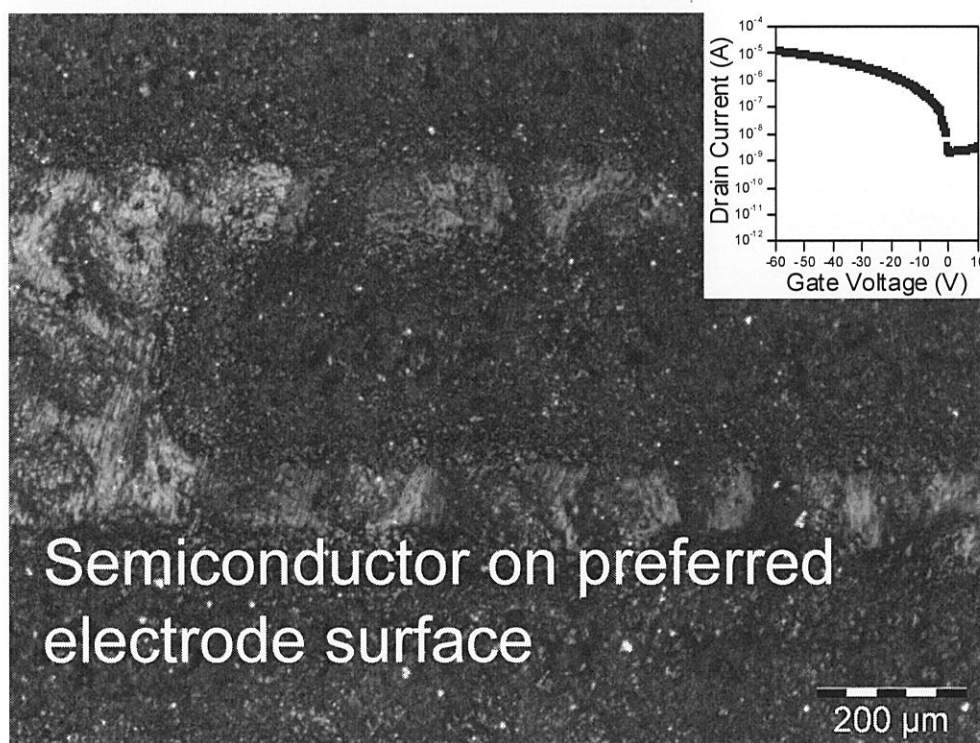
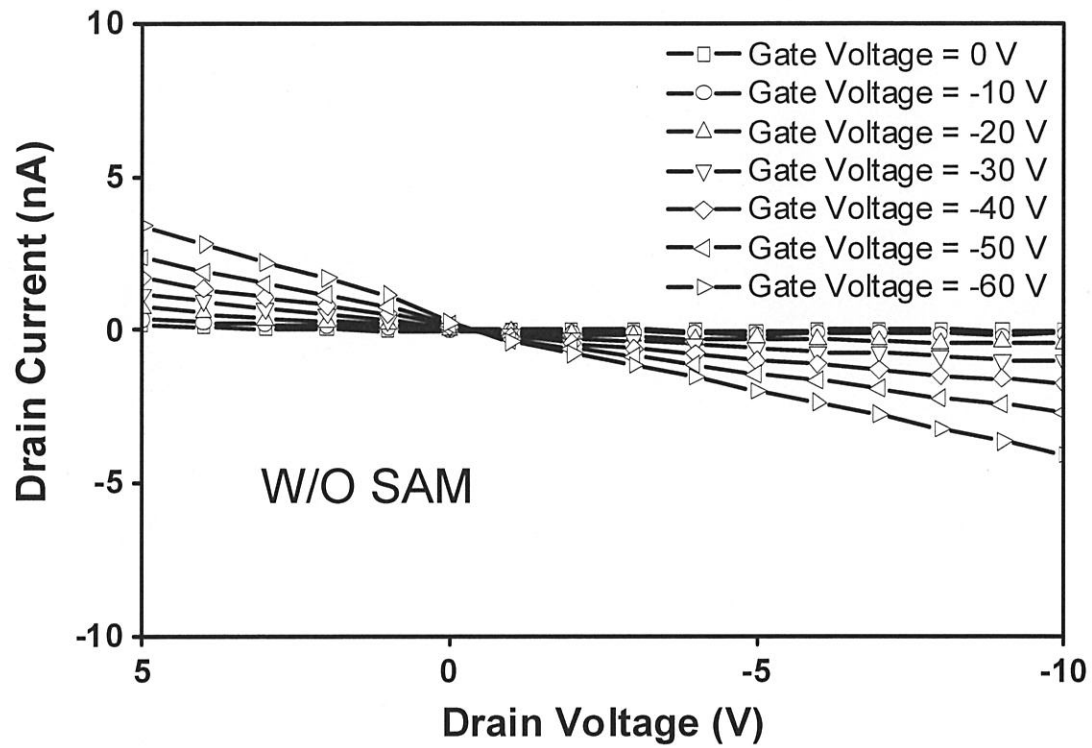


FIG. 4

(A)



(B)

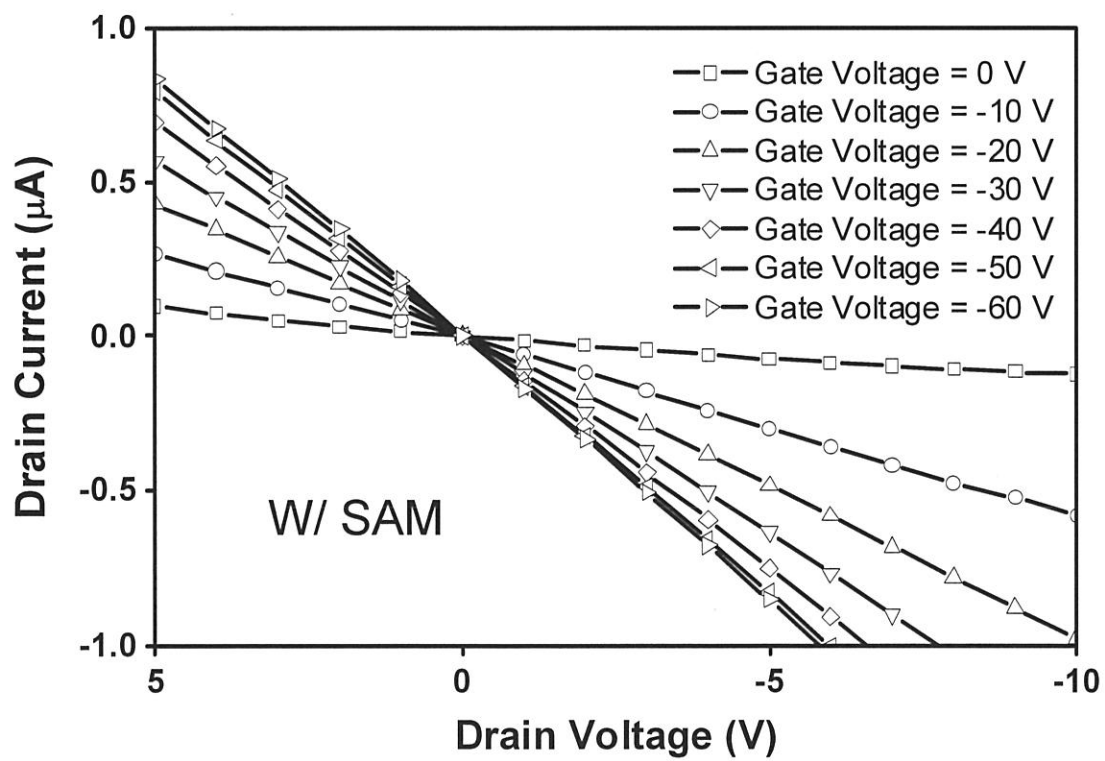
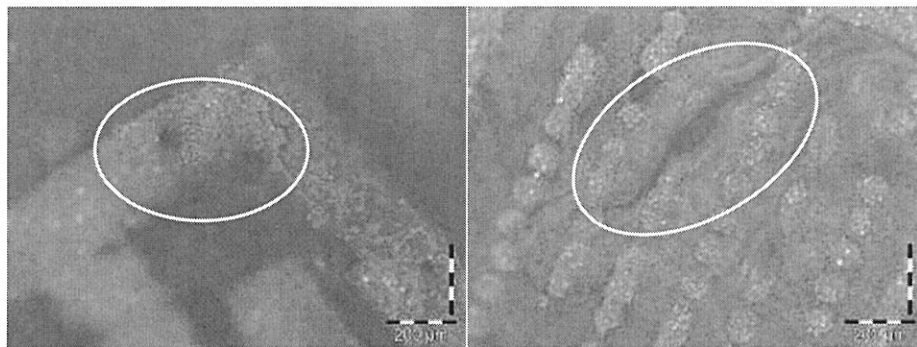
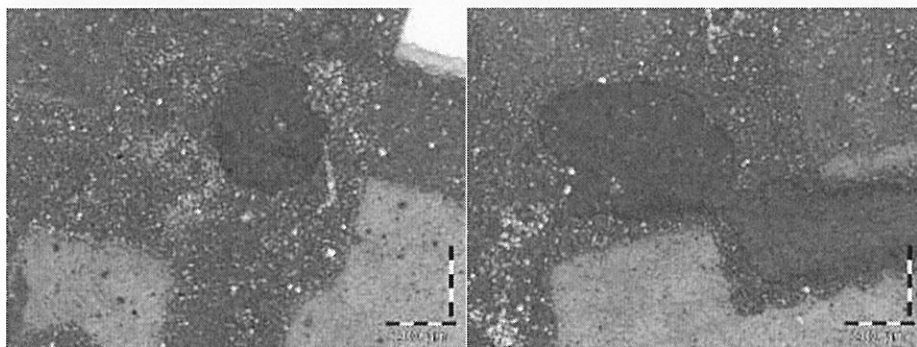


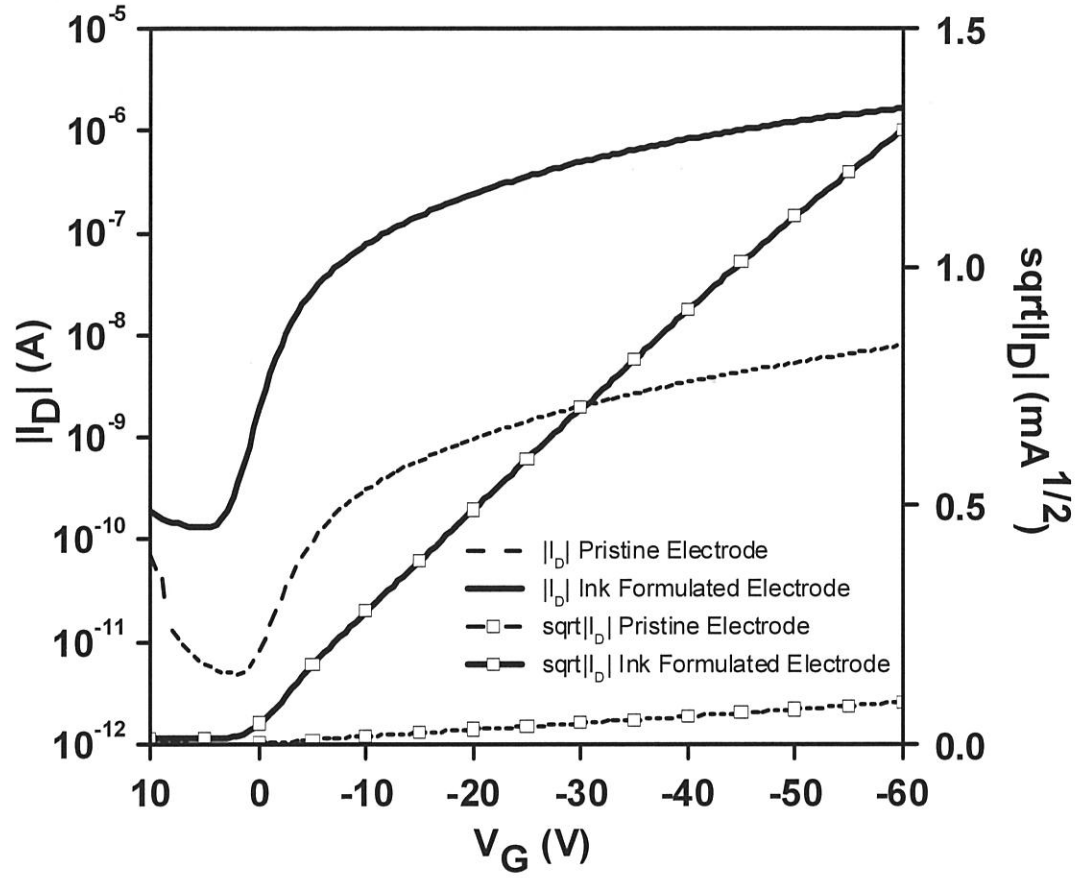
FIG. 5

(a) Damaged dielectrics by SAM solvent



(b) Damaged electrodes by SAM solvent

FIG. 6



Printed PFET	Device Mobility (cm ² V ⁻¹ s ⁻¹)
Pristine Electrode	2×10^{-4}
Ink Formulated Electrode	4×10^{-2}

FIG. 7

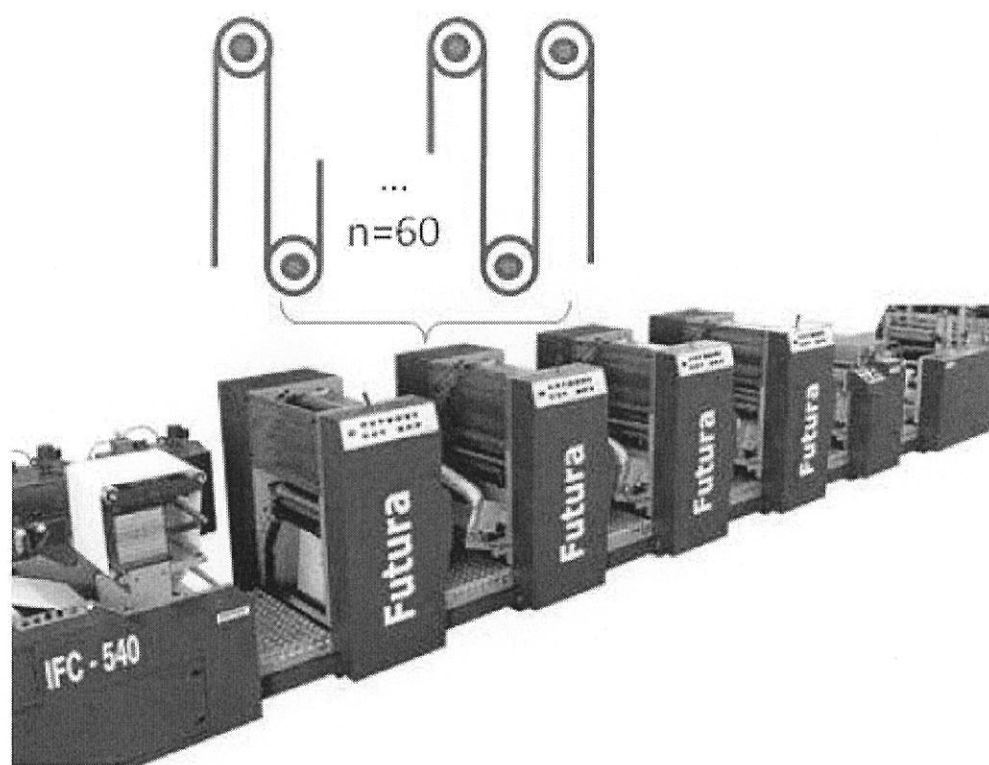
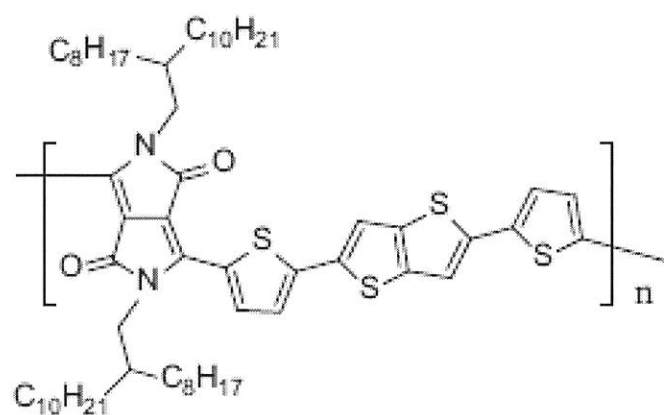
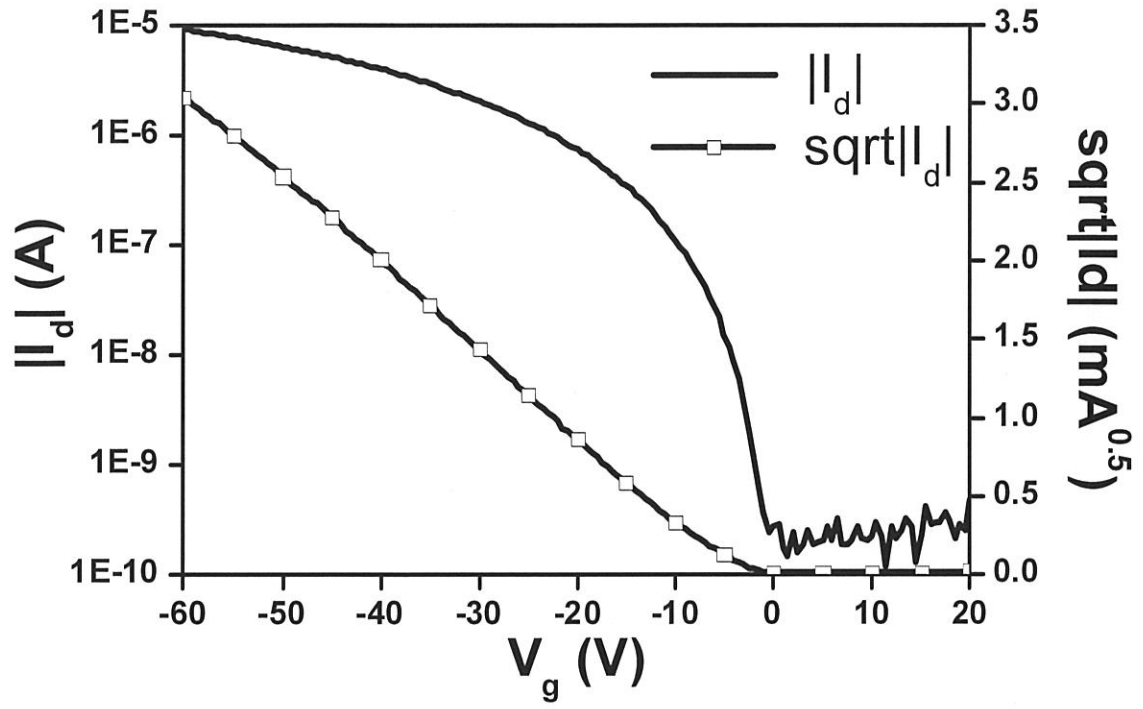


FIG. 8



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FIG. 9

(A)



(B)

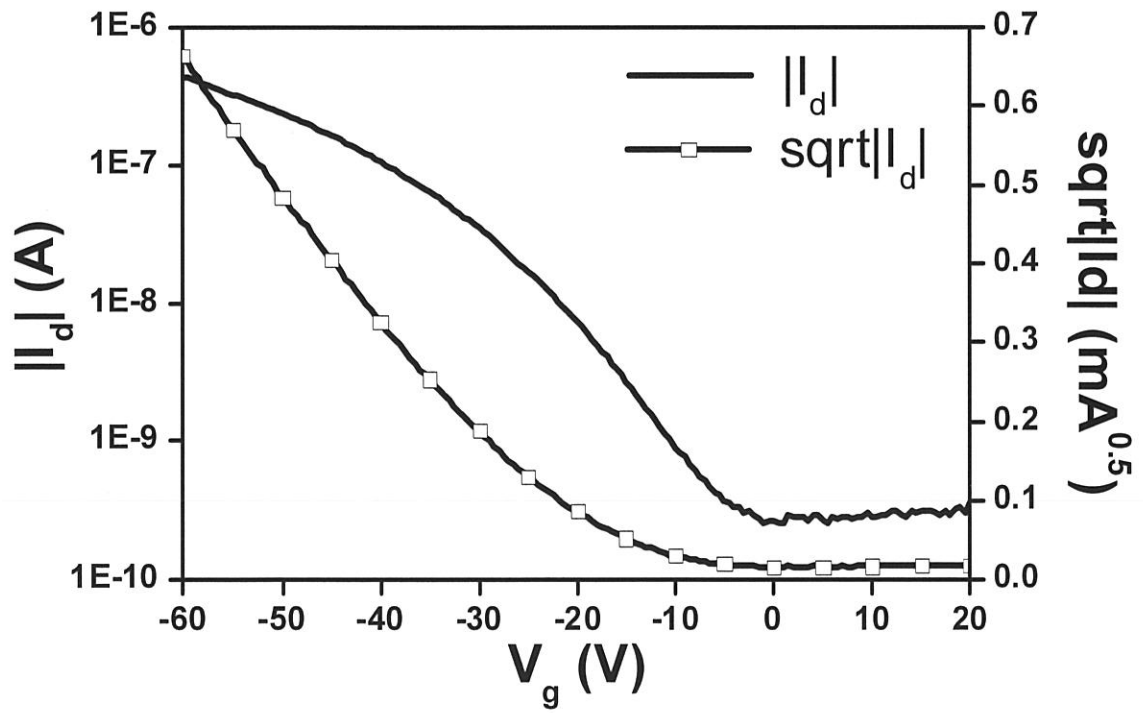


FIG. 9 (Cont.)**(C)**

Base structure	Semiconductor	Source/ Drain materials	Source/Drain modification	Mobility (cm ² /V.s)	V _t (V)	I _{on} /I _{off}
Printed Ag (Gate)/Printed Source/Drain	IMRE DPP polymer	Printed Ag	without modification	0.02-0.03	-20 to -30	1E3-1E4
Printed Ag (Gate)/Printed Source/Drain	IMRE DPP polymer	Printed Ag	Ag ink with SAM modification	0.6-1.0	-6 to 0.1	1E4